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(Contd.)
contact layer being thinner than the impurity layer and having a higher impurity concentration than the impurity layer;

a first electrode formed on the contact layer; and

a second electrode formed at another surface of the semiconductor substrate for

allowing a current to flow between the first and second electrodes.

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11. (Amended) The electrode contact section according to claim 7, wherein the impurity layer has a thickness of not more than 1.0 μm from the one surface of the semiconductor substrate.

12. (Amended) The electrode contact section according to claim 7, wherein the contact layer has a thickness of not more than 0.2 μm from the one surface of the semiconductor substrate.

13. (Twice Amended) The electrode contact section according to claim 7, wherein: the silicide layer has a thickness of not more than 0.2 μm from the one surface of the semiconductor substrate, and

~~the silicide layer is thinner than the contact layer.~~

16. (Amended) A semiconductor device comprising:

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a first-conductivity-type semiconductor substrate;

a second-conductivity-type base region formed in one surface of the semiconductor substrate;

a first-conductivity-type impurity region formed in the base region;

a first electrode connected to the first-conductivity-type impurity region;

a gate electrode connected to the base region via an insulation film;

a second-conductivity-type impurity region formed in another surface of the semiconductor substrate and having a thickness of not more than 1.0 μm from the another surface of the semiconductor substrate;

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(concl.)

a second-conductivity-type contact region formed in the second-conductivity-type impurity region and having a thickness of not more than $0.2\ \mu\text{m}$ from the another surface of the semiconductor substrate, the contact region being thinner than the second-conductivity-type impurity region and having a higher impurity concentration than the second-conductivity-type impurity region; and

a second electrode formed on the contact region.

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18. (Amended) The semiconductor device according to claim 16, wherein the second-conductivity-type impurity region is formed in the entire another surface of the semiconductor substrate.

19. (Amended) The semiconductor device according to claim 16, wherein the impurity region is formed in a portion less than the entire another surface of the semiconductor substrate.

20. (Amended) A semiconductor device comprising:

- a first-conductivity-type semiconductor substrate;
- a second-conductivity-type base region formed in one surface of the semiconductor substrate;
- a first-conductivity-type impurity region formed in the base region;
- a first electrode connected to the first-conductivity-type impurity region;
- a gate electrode connected to the base region via an insulation film;
- a second-conductivity-type impurity region formed in another surface of the semiconductor substrate;

a second-conductivity-type contact region formed in the impurity region, the second-conductivity-type contact region being thinner than the second-conductivity-type impurity region and having a higher impurity concentration than the second-conductivity-type impurity region;

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(Contd)

a second electrode formed on the contact region; and

a silicide region formed between the second electrode and the contact region, the silicide region having a contact-region-side end thereof made to substantially correspond to that portion of the contact region at which a concentration profile of the contact region assumes a peak value.

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22. (Amended) The semiconductor device according to claim 20, wherein the second-conductivity-type impurity region has a thickness of not more than 1.0 μm from the another surface of the semiconductor substrate.

23. (Amended) The semiconductor device according to claim 20, wherein the contact region has a thickness of not more than 0.2 μm from the another surface of the semiconductor substrate.

24. (Amended) The semiconductor device according to claim 20, wherein:

the silicide region has a thickness of not more than 0.2 μm from the another surface of the semiconductor substrate, and

the silicide layer is thinner than the contact region.

25. (Amended) The semiconductor device according to claim 20, wherein the second-conductivity-type impurity region is formed in the entire another surface of the semiconductor substrate.

26. (Amended) The semiconductor device according to claim 20, wherein the second-conductivity-type impurity region is formed in a portion less than the entire another surface of the semiconductor substrate.

REMARKS

Favorable reconsideration of this application is respectfully requested.

The specification has been amended to correct minor informalities.